

Switching (200V, 10A)

RDN100N20

●Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) Excellent resistance to damage from static electricity.

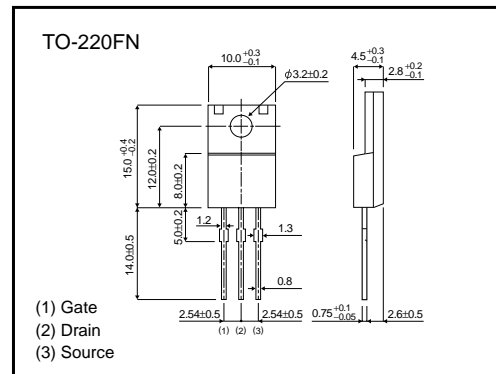
●Application

Switching

●Structure

Silicon N-channel
MOS FET

●External dimensions (Unit : mm)



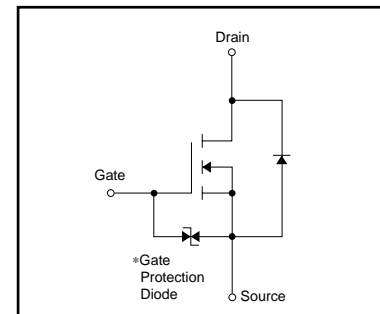
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	±30	V
Drain Current	Continuous	I_D	10 A
	Pulsed	I_{DP} *1	40 A
Reverse Drain Current	Continuous	I_{DR}	10 A
	Pulsed	I_{DRP} *1	40 A
Avalanche Current	I_{AS} *2	10	A
Avalanche Energy	E_{AS} *2	120	mJ
Total Power Dissipation (Tc=25°C)	P_D	35	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{slg}	-55 to +150	°C

*1 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*2 $L = 4.5mH$, $V_{DS} = 50V$, $R_G = 25\Omega$, 1Pulse, $T_{ch} = 25^\circ C$

●Equivalent circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} =±30V, V _{DS} =0V
Drain-Source Breakdown Voltage	V _{(BR)DSS}	200	—	—	V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	25	μA	V _{DS} =200V, V _{GS} =0V
Gate Threshold Voltage	V _{GS(th)}	2.0	—	4.0	V	V _{DS} =10V, I _D =1mA
Static Drain-Source On-State Resistance	R _{DS(on)}	—	0.27	0.36	Ω	I _D =5A, V _{GS} =10V
Forward Transfer Admittance	Y _{fs}	2.3	3.8	—	S	V _{DS} =10V, I _D =5A
Input Capacitance	C _{iss}	—	543	—	pF	V _{DS} =10V
Output Capacitance	C _{oss}	—	193	—	pF	V _{GS} =0V
Reverse Transfer Capacitance	C _{rss}	—	64	—	pF	f=1MHz
Turn-On Delay Time	t _{d(on)}	—	13	—	ns	I _D =5A, V _{DD} ≒100V
Rise Time	t _r	—	29	—	ns	V _{GS} =10V
Turn-Off Delay Time	t _{d(off)}	—	38	—	ns	R _L =20Ω
Fall Time	t _f	—	26	—	ns	R _{GS} =10Ω
Reverse Recovery Time	t _{rr}	—	133	—	ns	I _D =10A, V _{GS} =0V
Reverse Recovery Charge	Q _{rr}	—	0.54	—	μC	di / dt=100A / μs
Total Gate Charge	Q _g	—	15	—	nC	V _{DD} =100V, V _{GS} =10V, I _D =10A

●Electrical characteristic curves

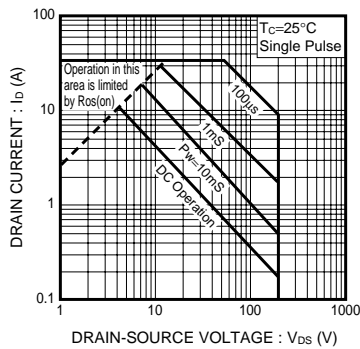


Fig.1 Maximum Safe Operating Area

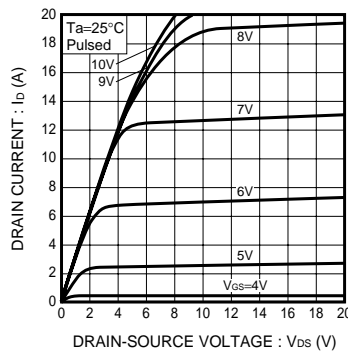


Fig.2 Typical Output Characteristics

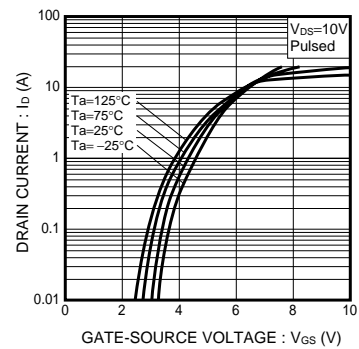


Fig.3 Typical Transfer Characteristics

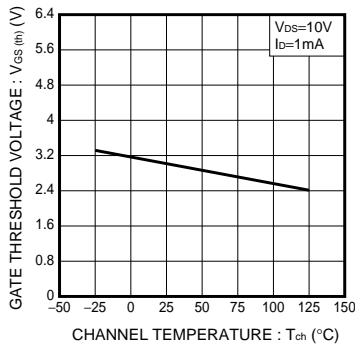


Fig.4 Gate Threshold Voltage vs. Channel Temperature

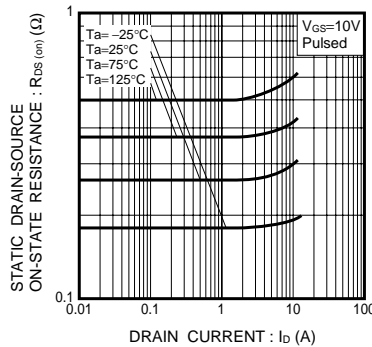


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

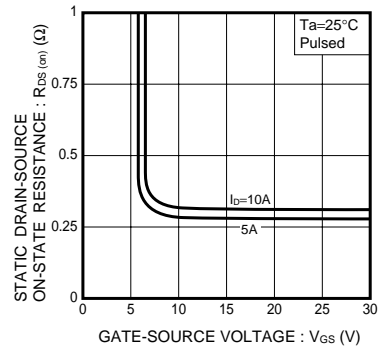


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

Transistors

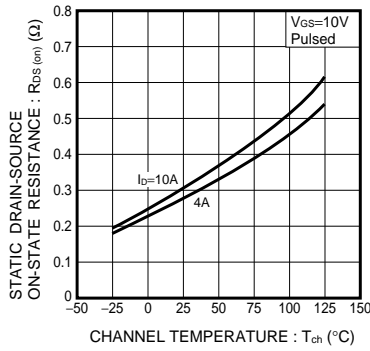


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

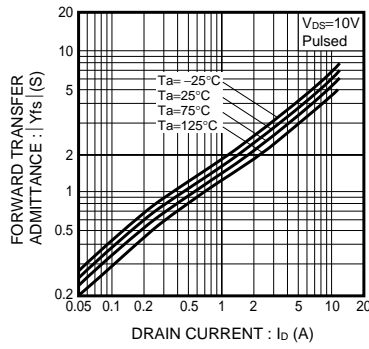


Fig.8 Forward Transfer Admittance vs. Drain Current

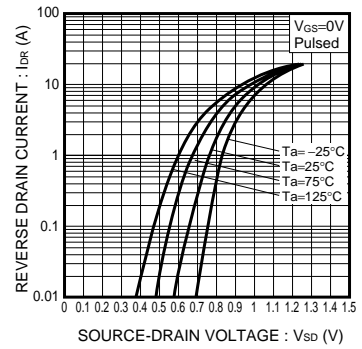


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

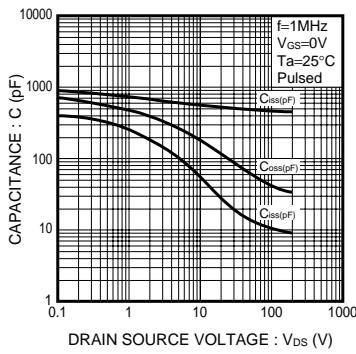


Fig.10 Typical Capacitance vs. Drain-Source Voltage

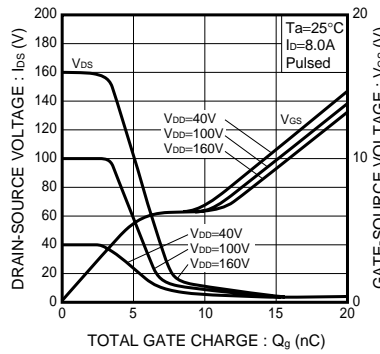


Fig.11 Dynamic Input Characteristics

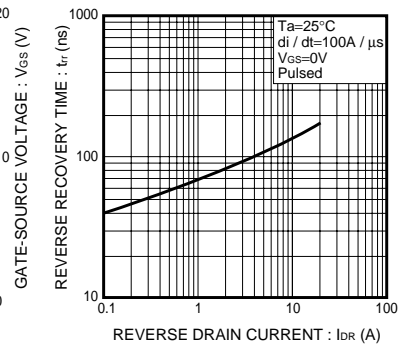


Fig.12 Reverse Recovery Time vs. Reverse Drain Current

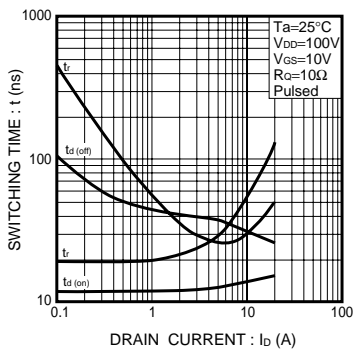


Fig.13 Switching Characteristics

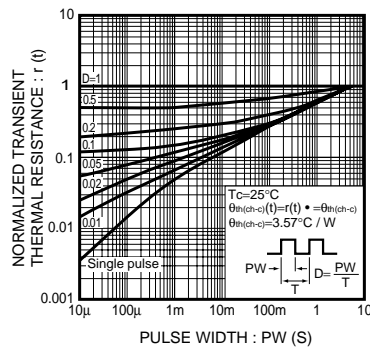


Fig.14 Normalized Transient Thermal Resistance vs. Pulse Width

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